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November 2013

FQP27N25

N-Channel QFET[®] MOSFET 250 V, 25.5 A, 110 m Ω

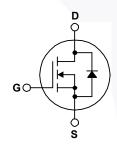
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 25.5 A, 250 V, $R_{DS(on)}$ = 110 m Ω (Max.) @ V_{GS} = 10 V, I_D = 12.75 A
- Low Gate Charge (Typ. 50 nC)
- · Low Crss (Typ. 45 pF)
- · 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP27N25	Unit
V_{DSS}	Drain-Source Voltage		250	V
I _D	Drain Current - Continuous (T _C = 25°C	:)	25.5	Α
	- Continuous (T _C = 100°	C)	16.2	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	102	Α
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	600	mJ
I _{AR}	Avalanche Current	(Note 1)	25.5	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	18	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
P _D	Power Dissipation (T _C = 25°C)		180	W
	- Derate above 25°C		1.43	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQP27N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP27N25	FQP27N25	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	250			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.29		V/°C
I _{DSS}	99	V _{DS} = 250 V, V _{GS} = 0 V			1	μΑ
Zero Gate Voltage Drain Current	V _{DS} = 200 V, T _C = 125°C			10	μΑ	
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	aracteristics			•		
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 12.75 A		0.083	0.11	Ω
g _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 12.75 A		24		S
Dynam C _{iss}	mic Characteristics Input Capacitance V _{DS} = 25 V, V _{GS} = 0 V,			1900	2450	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		360	470	pF
C _{rss}	Reverse Transfer Capacitance			45	60	pF
Switch	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V = 425 V I = 27 A		32	75	ns
t _r	Turn-On Rise Time	$V_{DD} = 125 \text{ V}, I_{D} = 27 \text{ A},$ $R_{G} = 25 \Omega$		270	550	ns
t _{d(off)}	Turn-Off Delay Time	1\(\text{G} = 20 \(\text{22}\)		80	170	ns
t _f	Turn-Off Fall Time	(Note 4)	/	120	250	ns
Qg	Total Gate Charge	V _{DS} = 200 V, I _D = 27 A,		50	65	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	/ 	12.5		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		26		nC
	Source Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				25.5	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	Forward Current			102	Α
- ••						

Q_{rr}

 V_{SD}

 t_{rr}

Notes: Notes: Notes: A Repetitive Rating: Pulse width limited by maximum junction temperature.
2. L = 1.5 mH, I_{AS} = 25.5 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.
3. I_{SD} \leq 27 A, di/dt \leq 300 A/µs, V_{DD} \leq BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature.

Drain-Source Diode Forward Voltage

Reverse Recovery Time

Reverse Recovery Charge

1.5

220

1.8

V

ns

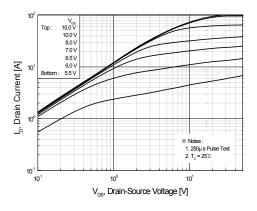
μС

 $V_{GS} = 0 \text{ V}, I_{S} = 25.5 \text{ A}$

 $V_{GS} = 0 \text{ V}, I_{S} = 27 \text{ A},$

 $dI_F / dt = 100 A/\mu s$

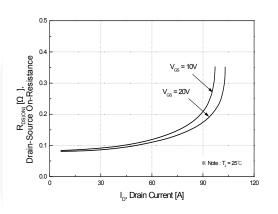
Typical Characteristics



V_{cs}, Gate-Source Voltage [V]

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



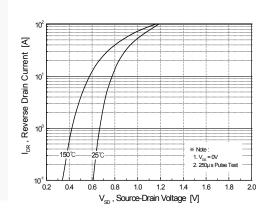
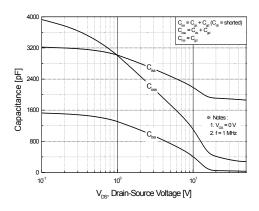


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



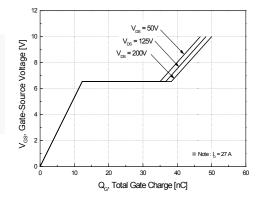


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

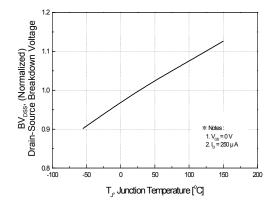
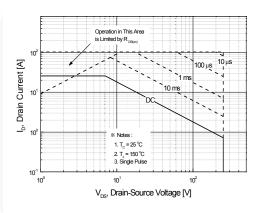


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



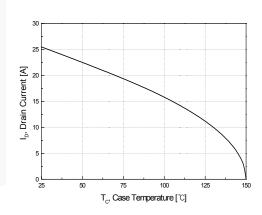


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

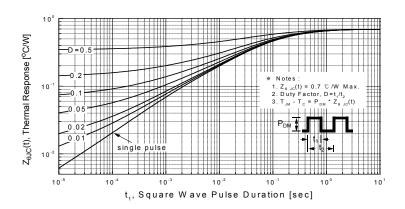


Figure 11. Transient Thermal Response Curve

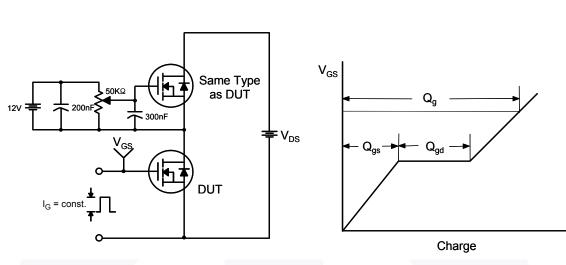


Figure 12. Gate Charge Test Circuit & Waveform

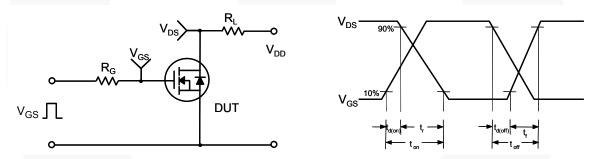


Figure 13. Resistive Switching Test Circuit & Waveforms

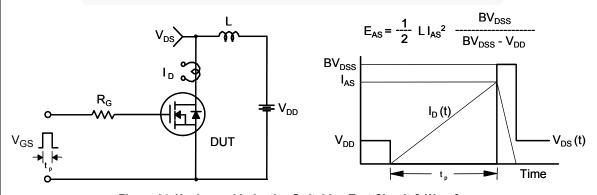
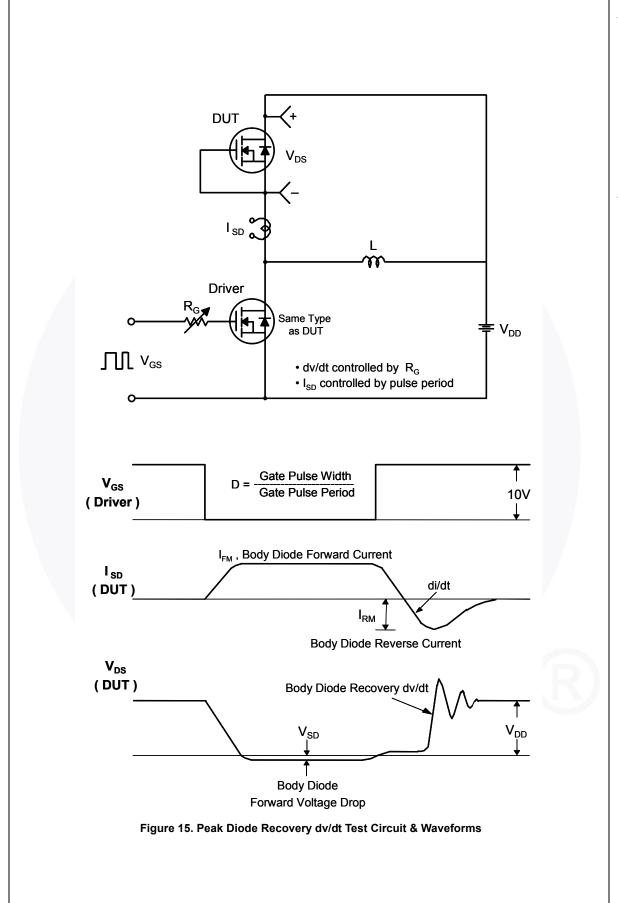
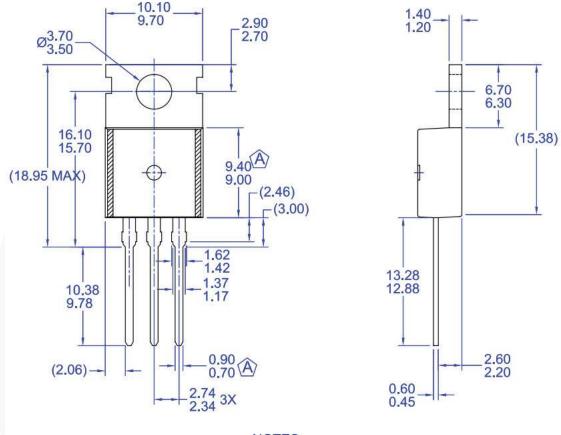


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions



4.70

10.20

9.80

NOTES:

- (A) CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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4.30





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